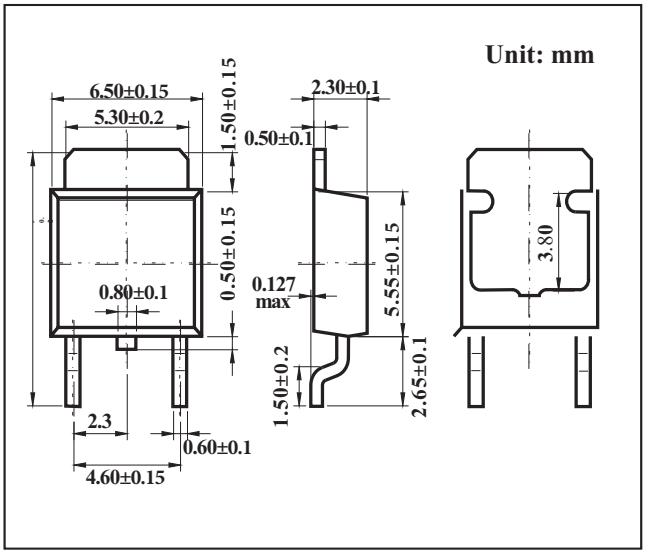
TO-252 Plastic-Encapsulate Transistors



FEATURES

- High Transiton Frequency: Ft=100MHz
- NPN Silicon Epitaxial Transistor

MECHANICAL DATA

- Case style:TO-252 molded plastic
- Mounting position:any

MAXIMUM RATINGS AND CHARACTERISTICS

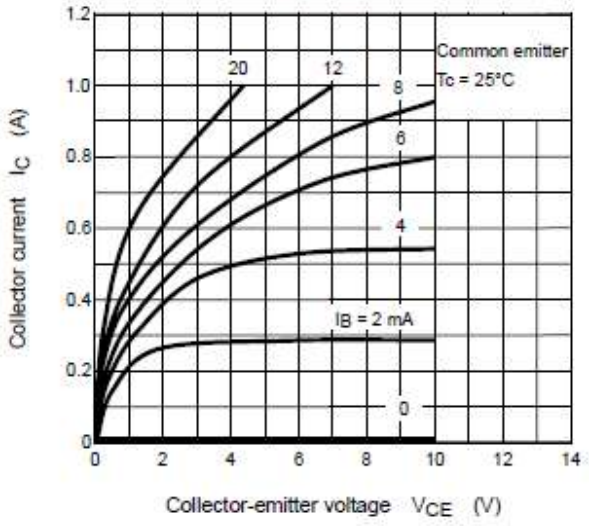
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector to base voltage	VCBO	160	V
Collector to emitter voltage	VCEO	160	V
Emitter to base voltage	VEBO	5	V
Collector current	I_C	1.5	A
Base Current	I_B	0.3	A
Total Power dissipation T_a = 25 ℃	PC	1	W
T_C = 25 ℃		15	W
Junction temperature	Tj	150	℃
Storage temperature	Tstg	-55 to +150	℃

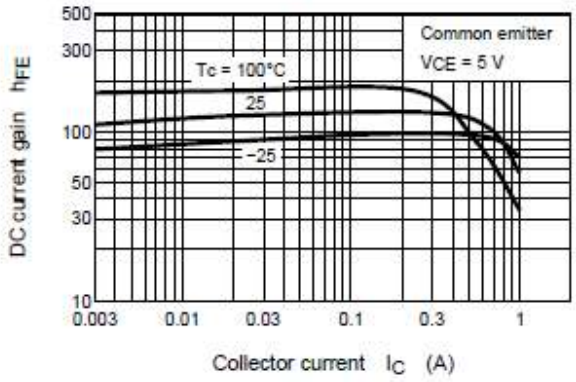
Parameter	Symbol	Test Conditons	Min	Typ	Max	Unit
collector cutoff current	ICBO	VCB=160V,IE=0			1	uA
emitter cutoff current	IEBO	VEB=5V,IC=0			1	uA
Collector-Emitter Breakdown Voltage	V(BR)CEO	IC=10mA,IB=0	160			V
Emitter-Base Breakdown Voltage	V(BR)EBO	IE=1mA,IC=0	5			V
DC current Gain	Hfe	VCE=5V,IC=100mA	70		240	
Collector-Emitter Saturation Voltage	VCE(sat)	IC=500mA,IB=50mA			1.5	V
Base- Emitter Voltage	VBE	VCE=5V,IC=500mA			1	V
Transition Frequency	fT	VCE=10V,IC=100mA		100		MHz
Collector Output Capacitance	cob	VCB=10V.IE=0,f=1MHz		25		pF

RATINGS AND CHARACTERISTIC CURVES

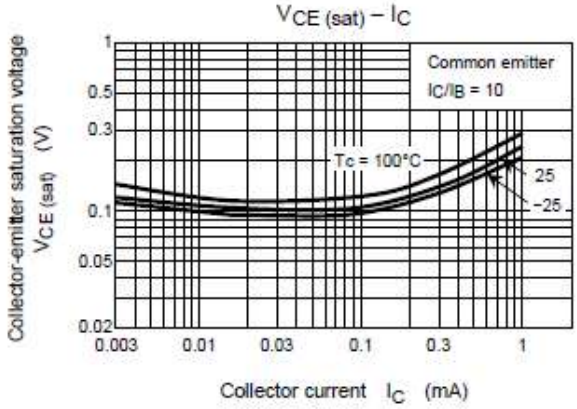
$I_C - V_{CE}$



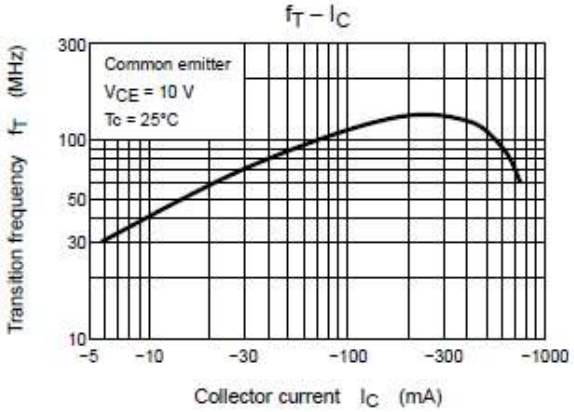
$h_{FE} - I_C$



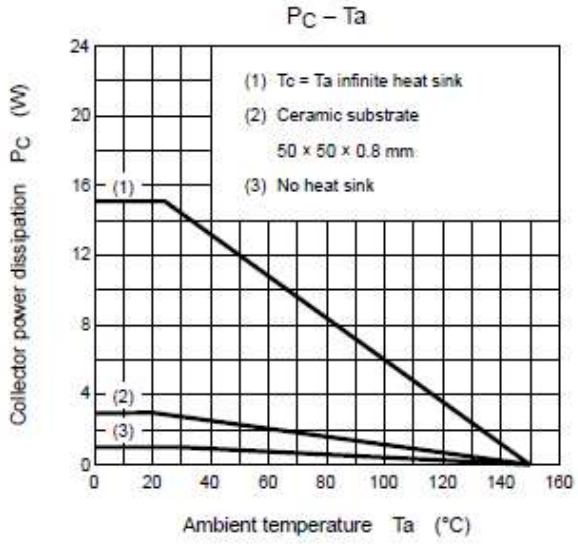
$V_{CE\ (sat)} - I_C$



$f_T - I_C$



$P_C - Ta$



Safe Operating Area